

Product data sheet

1. General description

Hyperfast power diode in a SOD142 (2-lead TO247) plastic package.

2. Features and benefits

- Low leakage current
- Low thermal resistance
- Low reverse recovery current
- Reduces switching losses in associated MOSFET or IGBT

3. Applications

- Active PFC in air conditioner
- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies

4. Quick reference data

Table 1. Qui	ck reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _R	reverse voltage	DC	-	-	600	V
I _{F(AV)}	average forward current	δ = 0.5; T _{mb} ≤ 115 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	-	30	A
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	-	270	A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	-	-	300	A
Static chara	acteristics					
V _F	forward voltage	I _F = 30 A; T _j = 25 °C; <u>Fig. 6</u>	-	2	2.75	V
		I _F = 30 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.38	1.8	V
Dynamic ch	naracteristics	·				
t _{rr}	reverse recovery time	I _F = 1 A; V _R = 30 V; dI _F /dt = 200 A/μs; T _j = 25 °C; <u>Fig. 7</u>	-	18	22	ns

5. Pinning information

Table 2. Pinning information							
Pin	Symbol	Description	Simplified outline	Graphic symbol			
1	К	cathode		K – K – A			
2	А	anode		001aaa020			
mb	mb	mounting base; connected to cathode	TO-247 (SOD142)				

6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
BYC30W-600P	TO-247	Plastic Single-ended through-hole package; Heatsink mounted; 1 mounting hole; 2-lead TO-247	SOD142			

7. Marking

Table 4. Marking codes					
	Type number	Marking code			
	BYC30W-600P	BYC30W-600P			

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	600	V
V _{RWM}	crest working reverse voltage		-	600	V
V _R	reverse voltage	DC	-	600	V
I _{F(AV)}	average forward current	δ = 0.5; T _{mb} ≤ 115 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	30	A
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _{mb} ≤ 115 °C; square-wave pulse	-	60	A
I _{FSM}	non-repetitive peak forward current	t _p = 10 ms; T _{j(init)} = 25 °C; sine-wave pulse; <u>Fig. 4</u>	-	270	A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	-	300	A
T _{stg}	storage temperature		-65	175	°C
Tj	junction temperature		-	175	°C

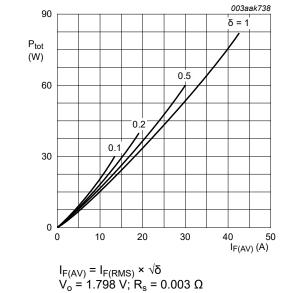
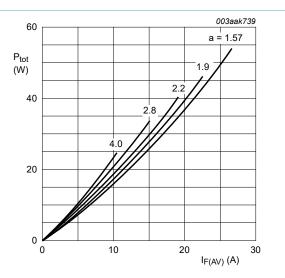


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



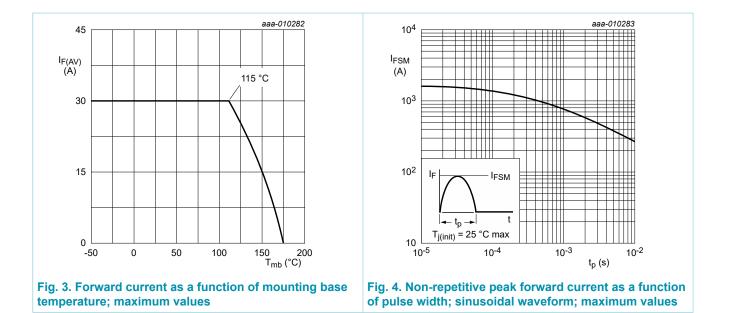
a = form factor = $I_{F(RMS)} / I_{F(AV)}$ $V_{o} = 1.798V; R_{s} = 0.003 \Omega$

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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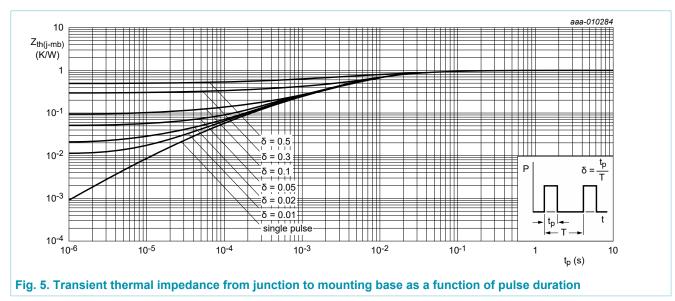
Hyperfast power diode



Hyperfast power diode

9. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	with heatsink compound; Fig. 5	-	-	1	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	45	-	K/W





Hyperfast power diode

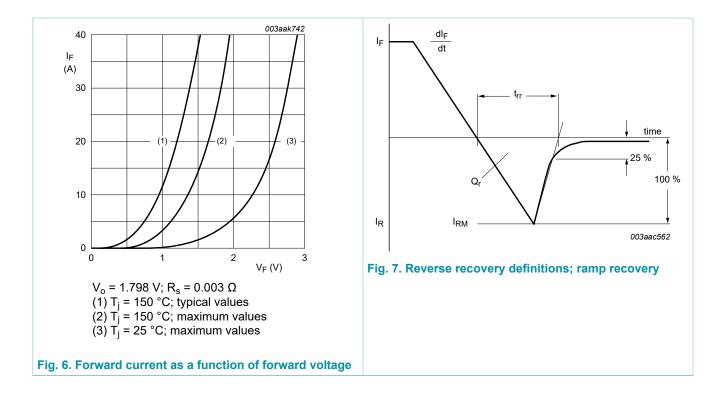
10. Characteristics

Table 7. Cha	racteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _F	forward voltage	I _F = 30 A; T _j = 25 °C; <u>Fig. 6</u>	-	2	2.75	V
		I _F = 30 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.38	1.8	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	-	10	μA
		V _R = 600 V; T _j = 150 °C	-	-	1	mA
Dynamic ch	naracteristics					
t _{rr}	reverse recovery time	I _F = 1 A; V _R = 30 V; dI _F /dt = 200 A/μs; T _j = 25 °C; <u>Fig. 7</u>	-	18	22	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ µs; $T_j = 25 \text{ °C}; \text{ Fig. 7}$	-	35	-	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ µs; $T_j = 125 \text{ °C}; Fig. 7$	-	70	-	ns
		$I_F = 30 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/$ µs; $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{2}$	-	29	-	ns
I _{RM}	peak reverse recovery current	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ µs; $T_j = 25 \text{ °C}; \text{ Fig. 7}$	-	3.5	-	A
		I _F = 30 A; V _R = 200 V; dI _F /dt = 200 A/ μs; T _i = 125 °C; <u>Fig. 7</u>	-	7.6	-	А
Qr	recovered charge	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 25 \text{ °C}; Fig. 7$	-	50	-	nC
		I _F = 30 A; V _R = 200 V; dI _F /dt = 200 A/ μs; T _i = 125 °C; <u>Fig. 7</u>	-	280	-	nC

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11. Package outline

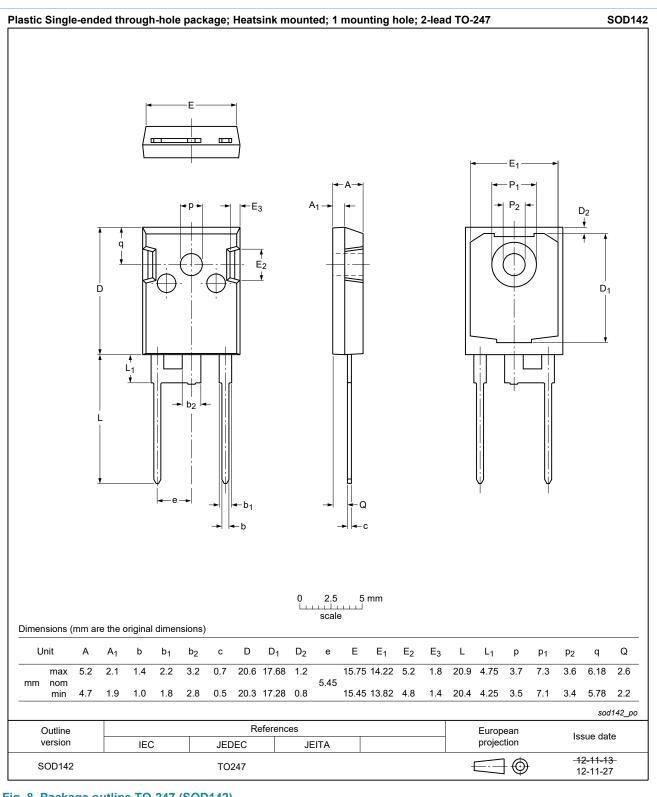


Fig. 8. Package outline TO-247 (SOD142)

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12. Legal information

Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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[1] Please consult the most recently issued document before initiating or completing a design.

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